

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	"6747638"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 19:42
L2	2	I1 and gate and drain and source and (organic) and diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 19:47
L3	2	I2 and data and scan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 19:47
L4	3325	gate and drain and source and (organic) and diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:44
L5	576	I4 and data and scan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 20:11
L6	451	I5 and @ad<="20031009"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 20:12
L7	174	pixel and dope\$1 and region and I6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 19:49
L8	143	capacit\$4 and I7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 20:12
L9	157	I4 and data near line and scan near line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 21:11

L10	113	I9 and @ad<="20031009"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:46
L11	96	capacit\$4 and I10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 20:25
L12	14	I11 and dope\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 20:26
L13	560	gate and drain and source and (organic) and diode and (LDD)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 21:11
L14	453	I13 and @ad<="20031009"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 21:24
L15	8	I14 and data near line and scan near line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 21:23
L16	102	organic and diode and (light\$2 near doped near drain or LDD) and scan and data	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 21:24
L17	65	I16 and concentrat\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 21:24
L18	54	I17 and @ad<="20031009"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:11
L19	45	I18 and n near type and p near type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:14

L20	3430267	I18 and n near type and p near type and poly-silicon thin film "transistor."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:14
L21	0	I18 and n near type and p near type and poly-silicon near thin near film near transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:15
L22	2	I18 and n near type and p near type and poly-silicon and thin near film near transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:15
L23	0	gate and drain and source and (organic) and diode and dat near line\$1 and scan near line\$1 and (light\$2 near dope\$1 near drain or LDD)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:46
L24	23	gate and drain and source and (organic) and diode and data near line\$1 and scan near line\$1 and (light\$2 near dope\$1 near drain or LDD)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:46
L25	0	I23 and @ad<="20031009"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:49
L26	18	I24 and @ad<="20031009"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:51
L27	17	type and silicon and I26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/21 22:51